

(12) INTERNATIONAL APPLICATION PUBLISHED UNDER THE PATENT COOPERATION TREATY (PCT)

(19) World Intellectual Property

Organization

International Bureau

(43) International Publication Date

24 October 2019 (24.10.2019)



(10) International Publication Number

WO 2019/201623 A2

(51) International Patent Classification:

C25D 3/12 (2006.01)

C25D 7/12 (2006.01)

C25D 3/16 (2006.01)

(21) International Application Number:

PCT/EP2019/058617

(22) International Filing Date:

05 April 2019 (05.04.2019)

(25) Filing Language:

English

(26) Publication Language:

English

(30) Priority Data:

18168249.3

19 April 2018 (19.04.2018)

EP

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(81) Designated States (unless otherwise indicated, for every kind of national protection available): AE, AG, AL, AM, AO, AT, AU, AZ, BA, BB, BG, BH, BN, BR, BW, BY, BZ, CA, CH, CL, CN, CO, CR, CU, CZ, DE, DJ, DK, DM, DO, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM, GT, HN, HR, HU, ID, IL, IN, IR, IS, JO, JP, KE, KG, KH, KN, KP, KR, KW, KZ, LA, LC, LK, LR, LS, LU, LY, MA, MD, ME, MG, MK, MN, MW, MX, MY, MZ, NA, NG, NI, NO, NZ, OM, PA, PE, PG, PH, PL, PT, QA, RO, RS, RU, RW, SA, SC, SD, SE, SG, SK, SL, SM, ST, SV, SY, TH, TJ, TM, TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, ZA, ZM, ZW.

(84) Designated States (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LR, LS, MW, MZ, NA, RW, SD, SL, ST, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, RU, TJ, TM), European (AL, AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HR, HU, IE, IS, IT, LT, LU, LV, MC, MK, MT, NL, NO, PL, PT, RO, RS, SE, SI, SK, SM, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, KM, ML, MR, NE, SN, TD, TG).

Declarations under Rule 4.17:

- as to applicant's entitlement to apply for and be granted a patent (Rule 4.17(ii))
- of inventorship (Rule 4.17(iv))

Published:

- without international search report and to be republished upon receipt of that report (Rule 48.2(g))

(54) Title: COMPOSITION FOR COBALT OR COBALT ALLOY ELECTROPLATING

(57) Abstract: A cobalt electroplating composition comprising: (a) cobalt ions, (b) an ammonium compound of formula $(NR^1R^2R^3H^+)_nX^{n-}$ wherein R^1, R^2, R^3 are independently selected from H and linear or branched C_1 to C_6 alkyl, X is selected from an n valent inorganic or organic counter ion, n is an integer selected from 1, 2 or 3.



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Composition for cobalt or cobalt alloy electroplating

The present invention relates to a composition for cobalt or cobalt alloy electroplating.

5 Background of the Invention

Filling of small features, such as vias and trenches, by metal electroplating is an essential part of the semiconductor manufacture process. It is well known, that the presence of organic substances as additives in the electroplating bath can be crucial in
10 achieving a uniform metal deposit on a substrate surface and in avoiding defects, such as voids and seams, within the metal lines.

With further decreasing aperture size of recessed features like vias or trenches the filling of the interconnects with copper becomes especially challenging, also since the
15 copper seed deposition by physical vapor deposition (PVD) prior to the copper electrodeposition might exhibit inhomogeneity and non-conformity and thus further decreases the aperture sizes particularly at the top of the apertures. Furthermore, it becomes more and more interesting to substitute copper by cobalt since cobalt shows less electromigration into the dielectric.

20 WO 2017/004424 discloses a composition for cobalt electroplating into interconnect features comprising an acetylenic suppressor compound and preferably a buffer. A preferred buffer is boric acid. The only example comprises boric acid, too.

25 DE 10 2014 019753 A1 discloses a boric acid free nickel electroplating bath comprising ammonium chloride.

JP 62-103387 A discloses an electroplating bath for depositing metals like Ni, Co, Fe, etc. which comprises a buffer. The Co composition in example 10 comprises citrate as
30 the buffer.

On the other hand, cobalt may also be a substitute of copper in other applications like under bump metallization. In this case much bigger structures comprising micrometer-sized aperture size are used. Besides a void free filling in this application it is of
35 particular importance that all features are equally filled with cobalt so that all bump on which the solders are to be deposited show essentially the same height.

A disadvantage of the existing cobalt electrodeposition baths is the pronounced non-uniformity of the electrodeposited cobalt layer.

40 There is still a strong need for a cobalt electroplating bath which provides, besides void-free filling of submicrometer-sized interconnects, a substantially planar surface over the filled features. There is also a strong need for a cobalt electroplating bath

which provides a cobalt under bump metallization showing a low non-uniformity over the filled features.

It is therefore an object of the present invention to provide a composition useful for cobalt electrodeposition which improves the non-uniformity of the cobalt deposit across the wafer.

Summary of the Invention

It was found that it is possible to reduce the non-uniformity in cobalt electroplating compositions by using particular ammonium compounds as described below, particularly if applied to substrates comprising micrometer-sized solder bump features.

Therefore, the present invention provides a composition comprising

15

(a) cobalt ions,

(b) an ammonium compound of formula $(NR^1R^2R^3H^+)_nX^{n-}$

20 wherein

R^1, R^2, R^3 are independently selected from H and linear or branched C_1 to C_6 alkyl,
 X is selected from an n valent inorganic or organic counter ion,
 n is an integer selected from 1, 2 or 3.

25

The invention further relates to the use of a metal plating composition as defined herein for depositing cobalt into interconnect features or for providing a cobalt under bump metallization.

30 The invention further relates to a process for depositing a layer comprising cobalt on a substrate comprising features having an aperture size of 1 nanometer to 100 micrometers, by

a) contacting a composition as defined herein with the substrate, and
b) applying a current density to the substrate for a time sufficient to deposit a metal layer onto the substrate.

35

By using the ammonium compound according to the invention, the non-uniformity of the cobalt deposit across the wafer is significantly improved. A further advantage of the present invention is that by using the ammonium compounds described herein avoids the use of boric acid, which is a big advantage for health, safety and environmental reasons. Therefore, a further object of the present invention to provide a composition useful for cobalt electrodeposition which is boric acid free.

40

Detailed Description of the Invention

The compositions according to the inventions comprise cobalt ions, and an ammonium
5 compound as described below.

Ammonium compound

The cobalt or cobalt alloy electroplating composition comprises an ammonium
10 compound of formula $(NR^1R^2R^3H^+)_n X^{n-}$.

Herein, R^1 , R^2 , and R^3 are independently selected from H, linear or branched C_1 to C_6
alkyl. Preferably, R^1 , R^2 , and R^3 are independently selected from H and a linear or
branched C_1 to C_4 alkyl, particularly methyl and ethyl. More preferably at least one of
15 R^1 , R^2 and R^3 is H, even more preferably at least two of R^1 , R^2 and R^3 are H. Most
preferably, R^1 , R^2 , and R^3 are H.

X is an n valent inorganic or organic counter ion. Typical inorganic counter-ions are,
without limitation, chloride, sulfate (including hydrogen sulfate), phosphate (including
20 hydrogen and dihydrogen phosphate), and nitrate. Typical organic counter-ions are,
without limitation, C_1 to C_6 alkyl sulfonate, preferably methane sulfonate, C_1 to C_6
carboxylates, preferably acetate or citrate, phosphonate, sulfamate, etc. Inorganic
counter-ions are preferred. Chloride is the most preferred counter ions X since by using
chloride in combination with the ammonium cation the non-uniformity of the cobalt
25 deposit across the wafer may be further improved.

n is an integer selected from 1, 2 or 3 depending on the valence of the counter-ion. By
way of example, for chloride and hydrogen sulfate n would be 1, for sulfate or hydrogen
phosphate n would be 2 and for phosphate n would be 3.

30 Preferred ammonium compounds are ammonium sulfate, ammonium chloride, or
ammonium methane sulfonate,

Depending on the pH of the composition the amine compound may be completely or
35 partly protonated or deprotonated.

Preferably the cobalt or cobalt alloy electroplating composition is essentially free of
boric acid. Essentially free of boric acid as used herein means a boric acid content
below 0.1 g/l, preferably below 100 ppm by mass, most preferably the content of boric
40 acid is below the detection limit.

Suppressing agents

The plating composition may further comprise one or more suppressing agents (also referred to as suppressors).

5

Without limitation, typical suppressing agents are selected from the group consisting of: carboxymethylcellulose, nonylphenolpolyglycol ether, polyethylene glycoldimethyl ether, octandiolbis(polyalkylene glycol ether), octanol polyalkylene glycol ether, oleic acid polyglycol ester, polyethylene propylene glycol, polyethylene glycol, polyethyleneimine, polyethylene glycoldimethyl ether, polyoxypropylene glycol, polypropylene glycol, polyvinyl alcohol, stearic acid polyglycol ester, stearyl alcohol polyglycol ether, polyethylene oxide, ethylene oxide-propylene oxide copolymers, butyl alcohol-ethylene oxide-propylene oxide copolymers, 2-Mercapto-5-benzimidazolesulfonic acid, 2-mercaptobenzimidazole (MBI), benzotriazole, and combinations thereof.

15

In some embodiments, the suppressor includes one or more nitrogen atoms such as an amine group or an imine group. In some embodiments, the suppressor is a polymeric or oligomeric compound containing amine groups separated by a carbon aliphatic spacer such as CH_2CH_2 or $\text{CH}_2\text{CH}_2\text{CH}_2$. In a particular embodiment, the suppressor is polyethyleneimine (PEI, also known as polyaziridine, poly[imino(1,2-ethanediyl)], or poly(iminoethylene)). PEI has shown very good bottom-up fill characteristics in the context of cobalt deposition, as shown in the experimental results included herein.

25

Particularly preferred suppressing agents are those of formula I



30

to fill aperture sizes having nanometer or micrometer scale, in particular aperture sizes having 100 nanometers or less, 20 nm or less, 15 nm or less or even 7 nm or less.

35

Herein, R^1 is selected from X-Y, wherein X is a divalent spacer group selected from linear or branched C_1 to C_{10} alkanediyl, linear or branched C_2 to C_{10} alkenediyl, linear or branched C_2 to C_{10} alkynediyl, and $(\text{C}_2\text{H}_3\text{R}^6\text{-O})_m$. m is an integer selected from 1 to 30, preferably from 1 to 15, even more preferably from 1 to 10, most preferably from 1 to 5.

In a preferred embodiment X is selected from linear or branched C_1 to C_6 alkanediyl, preferably from C_1 to C_4 alkanediyl.

40

In a preferred embodiment X is selected from methanediyl, ethane-1,1-diyl and ethane-1,2-diyl. In a second preferred embodiment X is selected from propan-1,1-diyl, butane-1,1-diyl, pentane-1,1-diyl, and hexane-1,1-diyl. In a third preferred embodiment X is selected from propane-2,2-diyl, butane-2,2-diyl, pentane-2,2-diyl, and hexane-2,2-diyl.

In a fourth preferred embodiment X is elected from propane-1-2-diyl, butane-1,2-diyl, pentane-1,2-diyl, and hexane-1,2-diyl. In a fifth preferred embodiment X is elected from propane-1-3-diyl, butane-1,3-diyl, pentane-1,3-diyl, and hexane-1,3-diyl.

- 5 Y is a monovalent group and may be selected from OR^3 , with R^3 being selected from (i) H, (ii) C_5 to C_{20} aryl, preferably C_5 , C_6 , and C_{10} aryl, (iii) C_1 to C_{10} alkyl, preferably C_1 to C_6 alkyl, most preferably C_1 to C_4 alkyl (iv) C_6 to C_{20} arylalkyl, preferably C_6 to C_{10} arylalkyl, (v) C_6 to C_{20} alkylaryl, all of which may be substituted by OH, SO_3H , $COOH$ or a combination thereof, and (vi) $(C_2H_3R^6-O)_n-H$. In a preferred embodiment, R^3 may be
- 10 C_1 to C_6 alkyl or H. R^6 may be selected from H and C_1 to C_5 alkyl, preferably from H and C_1 to C_4 alkyl, most preferably H, methyl or ethyl.

- In another preferred embodiment, R^3 is selected from H to form a hydroxy group. In another preferred embodiment, R^3 is selected from polyoxyalkylene groups of formula
- 15 $(C_2H_3R^6-O)_n-H$. R^6 is selected from H and C_1 to C_5 alkyl, preferably from H and C_1 to C_4 alkyl, most preferably from H, methyl or ethyl. Generally, n may be an integer from 1 to 30, preferably from 1 to 15, most preferably from 1 to 10. In a particular embodiment polyoxymethylene, polyoxypropylene or a polyoxymethylene-co-oxypropylene may be used. In another preferred embodiment, R^3 may be selected from C_1 to C_{10} alkyl,
- 20 preferably from C_1 to C_6 alkyl, most preferably methyl and ethyl.

Furthermore, Y may be an amine group NR^3R^4 , wherein R^3 and R^4 are the same or different and may have the meanings of R^3 described for OR^3 above.

- 25 In a preferred embodiment, R^3 and R^4 are selected from H to form an NH_2 group. In another preferred embodiment, at least one of R^3 and R^4 , preferably both are selected from polyoxyalkylene groups of formula $(C_2H_3R^6-O)_n-H$. R^6 is selected from H and C_1 to C_5 alkyl, preferably from H and C_1 to C_4 alkyl, most preferably H, methyl or ethyl. In yet another preferred embodiment, at least one of R^3 and R^4 , preferably both are selected
- 30 from C_1 to C_{10} alkyl, preferably from C_1 to C_6 alkyl, most preferably methyl and ethyl.

- R^3 and R^4 may also together form a ring system, which may be interrupted by O or NR^7 . R^7 may be selected from R^6 and $X \equiv R^3$. Such ring system may preferably comprise 4 or 5 carbon atoms to form a 5 or 6 membered carbocyclic system. In such
- 35 carbocyclic system one or two of the carbon atoms may be substituted by oxygen atoms.

- Furthermore, Y may be a positively charged ammonium group $N^+R^3R^4R^5$. R^3 , R^4 , R^5 are the same or different and may have the meanings of R^3 described for OR^3 and
- 40 NR^3R^4 above. In a preferred embodiment R^3 , R^4 and R^5 are independently selected from H, methyl or ethyl.

m may be an integer selected from 1 to 30, preferably from 1 to 15, even more preferably from 1 to 10, most preferably from 1 to 5.

- In the additives of formula S1 R^2 may be either R^1 or R^3 as described above. If R^2 is R^1 , R^1 may be selected to form a symmetric compound (both R^1 s are the same) or an asymmetric compound (the two R^1 s are different).

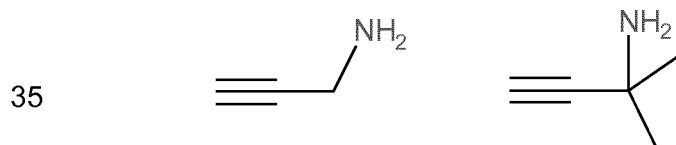
In a preferred embodiment R^2 is H.

- 10 Particularly preferred aminoalkynes are those in which
- (a) R^1 is $X-NR^3R^4$ and R^2 is H;
 - (b) R^1 is $X-NR^3R^4$ and R^2 is $X-NR^3R^4$ with X being selected from linear C_1 to C_4 alkanediyl and branched C_3 to C_6 alkanediyl;
- 15 Particularly preferred hydroxyalkynes or alkoxyalkynes are those in which
- (a) R^1 is $X-OR^3$ and R^2 is H;
 - (b) R^1 is $X-OR^3$ and R^2 is $X-OR^3$ with X being selected from linear C_1 to C_4 alkanediyl and branched C_3 to C_6 alkanediyl;
- 20 Particularly preferred alkynes comprising an amino and a hydroxy group are those in which R^1 is $X-OR^3$, particularly $X-OH$, and R^2 is $X-NR^3R^4$ with X being independently selected from linear C_1 to C_4 alkanediyl and branched C_3 to C_6 alkanediyl;

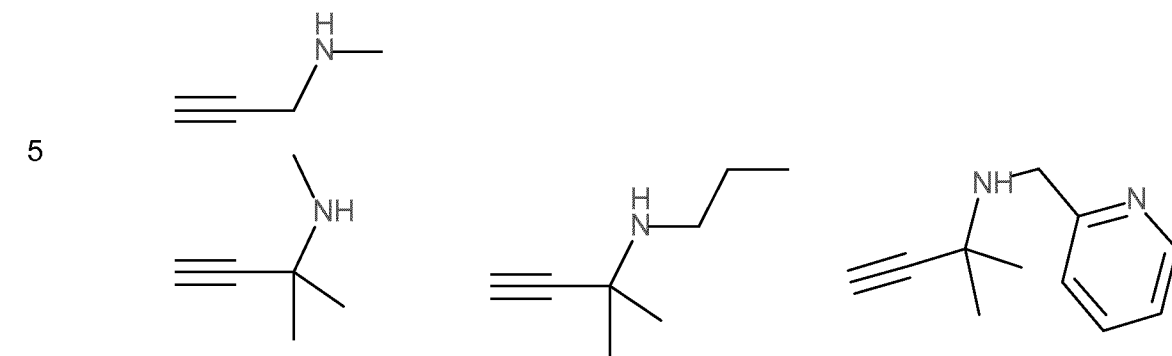
- The amine groups in the additives may be selected from primary (R^3 , R^4 is H) ,
 25 secondary (R^3 or R^4 is H) and tertiary amine groups (R^3 and R^4 are both not H).

- The alkynes may comprise one or more terminal triple bonds or one or more non-terminal triple bonds (alkyne functionalities). Preferably, the alkynes comprise one or more terminal triple bonds, particularly from 1 to 3 triple bonds, most preferably one
 30 terminal triple bond.

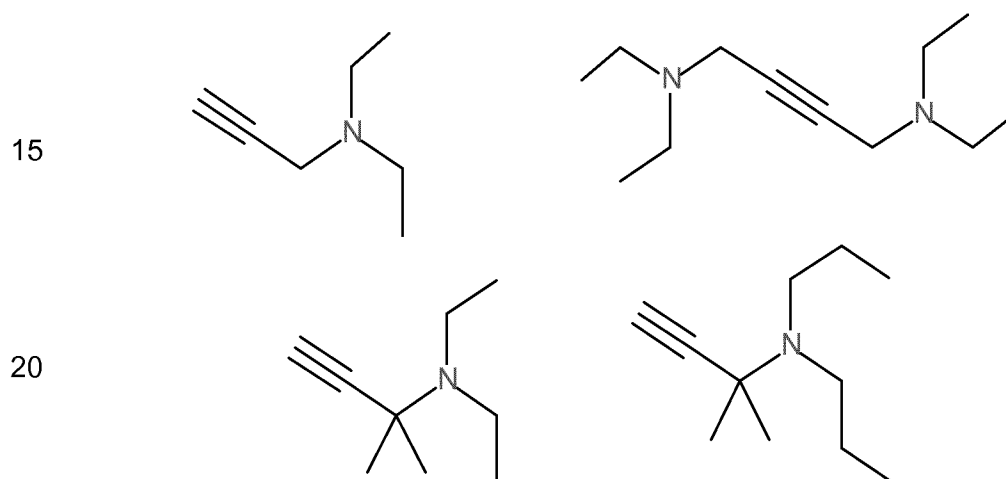
Particularly preferred specific primary aminoalkynes are:



Particularly preferred specific secondary aminoalkynes are:

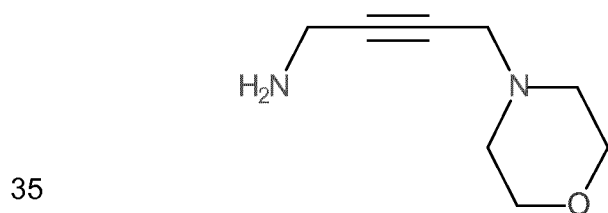


Particularly preferred specific tertiary aminoalkynes are:



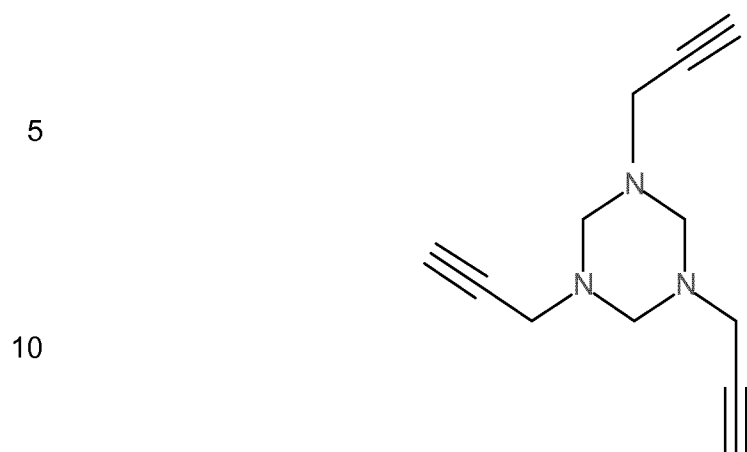
Other preferred additives are those in which the rests R^3 and R^4 may together form a ring system, which is optionally interrupted by O or NR^3 . Preferably, the rests R^3 and R^4 together form a C_5 or C_6 bivalent group in which one or two, preferably one, carbon atoms may be exchanged by O or NR^7 , with R^7 being selected from hydrogen, methyl or ethyl.

An example of such compounds is:



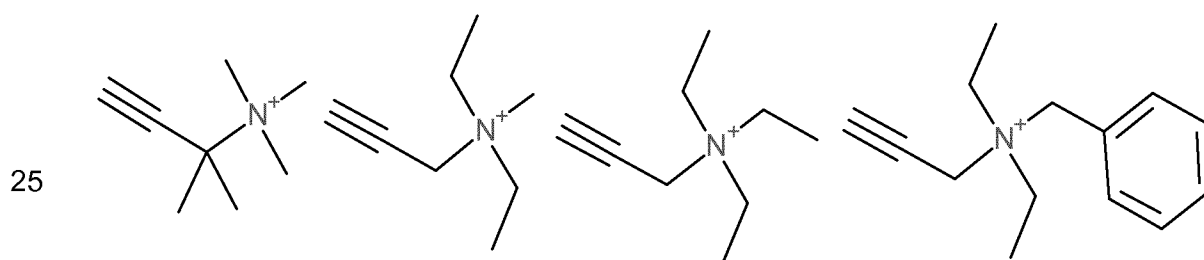
The first one may be received by reaction of propargyl amine with formaldehyde and morpholine, the second and third ones by reaction of propargyl alcohol with formaldehyde and piperidine or morpholine, respectively.

Another preferred additive comprising a saturated heterocyclic system is:

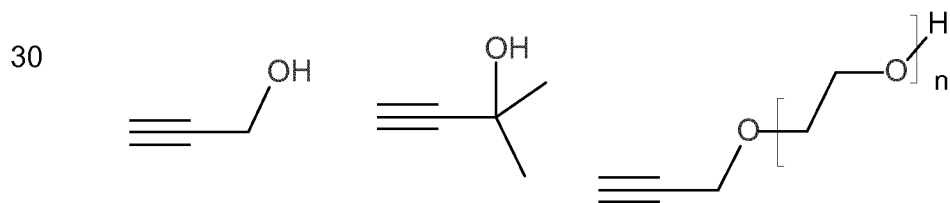


15 In this case R^3 and R^4 together form a ring system which is interrupted by two NR^3 groups, in which R^3 is selected from $CH_2-C\equiv C-H$. This additive comprises three terminal triple bonds.

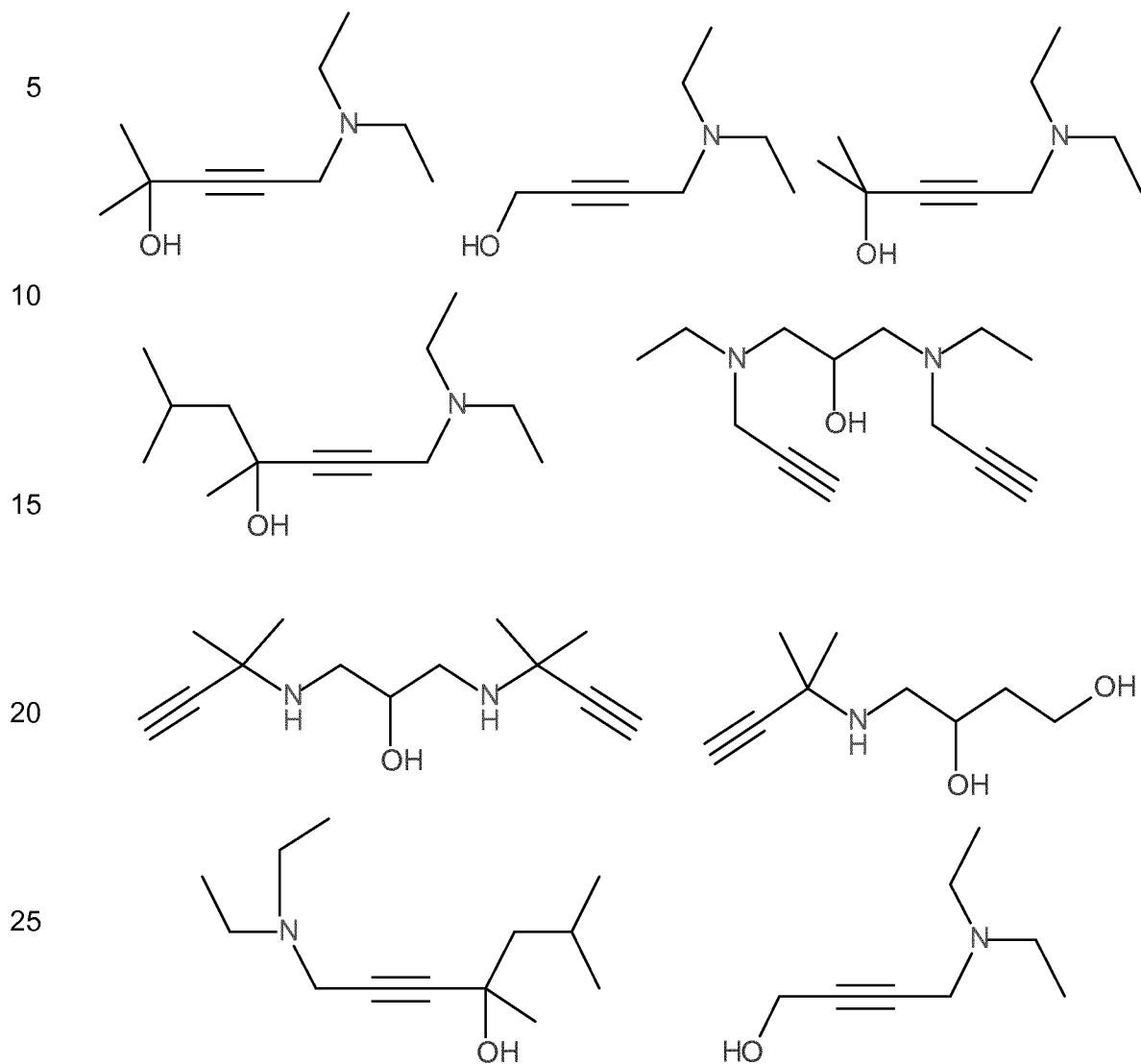
20 The amino groups in the additives may further be quaternized by reaction with alkylating agents such as but not limited to dialkyl sulphates like DMS, DES or DPS, benzyl chloride or chlormethylpyridine. Particularly preferred quaternized additives are:



Particularly preferred specific pure hydroxyalkynes are:



Particularly preferred specific aminoalkynes comprising OH groups are:

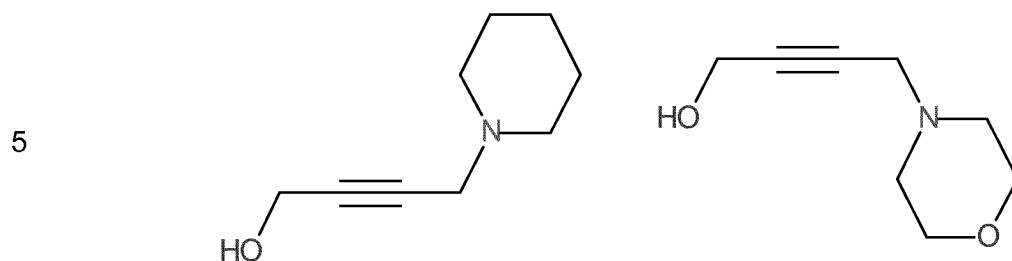


Also in this case the rests R^3 and R^4 may together form a ring system, which is optionally interrupted by O or NR^3 . Preferably, the rests R^3 and R^4 together form a C_5 or C_6 bivalent group in which one or two, preferably one, carbon atoms may be exchanged by O or NR^7 , with R^7 being selected from hydrogen, methyl or ethyl.

35

40

Examples for such compounds are:



10 These may be received by reaction of propargyl alcohol with formaldehyde and piperidine or morpholine, respectively.

By partial reaction with alkylating agents mixtures of additives may be formed. In one embodiment, such mixtures may be received by reaction of 1 mole diethylaminopropyne and 0.5 mole epichlorohydrin, 1 mole diethylaminopropyne and 0.5 mole benzylchloride, 1 mole diethylaminopropyne with 0.9 mole dimethyl sulphate, 1 mole dimethyl propyne amine and 0.33 mole dimethyl sulphate, or 1 mole dimethyl propyne amine and 0.66 mole dimethyl sulphate. In another embodiment such mixtures may be received by reaction of 1 mole dimethyl propyne amine and 1.5, 1.9, or 2.85 mole dimethyl sulphate, 1 mole dimethyl propyne amine and 0.5 mole epichlorohydrin, 1 mole dimethyl propyne amine and 2.85 diethyl sulphate, or 1 mole dimethyl propyne amine and 1.9 mole dipropyl sulphate.

15

20

In a further embodiment, the suppressing agents may be substituted by SO₃H (sulfonate) groups or COOH (carboxy) groups. Specific sulfonated additives may be but are not limited to butynoxy ethane sulfonic acid, propynoxy ethane sulfonic acid, 1,4-di-(β-sulfoethoxy)-2-butyne, 3-(β-sulfoethoxy)-propyne.

25

In general, the total amount of the suppressing agents in the electroplating bath is from 0.5 ppm to 10000 ppm based on the total weight of the plating bath. The suppressing agents are typically used in a total amount of from about 0.1 ppm to about 1000 ppm based on the total weight of the plating bath and more typically from 1 to 100 ppm, although greater or lesser amounts may be used. Preferred concentration ranges are for example between about 10-60 ppm, or between about 15-60 ppm, or between about 30-60 ppm. In this context, parts per million (ppm) is a mass fraction of the suppressor molecules in the electrolyte. In some cases, the suppressor may have a concentration of at least about 10 ppm, or at least about 15 ppm, or at least about 20 ppm, or at least about 30 ppm, or at least about 50 ppm. In these or other cases, the suppressor may have a concentration of about 1,000 ppm or less, for example about 500 ppm or less, about 100 ppm or less, about 75 ppm or less, about 60 ppm or less, or about 50 ppm or less.

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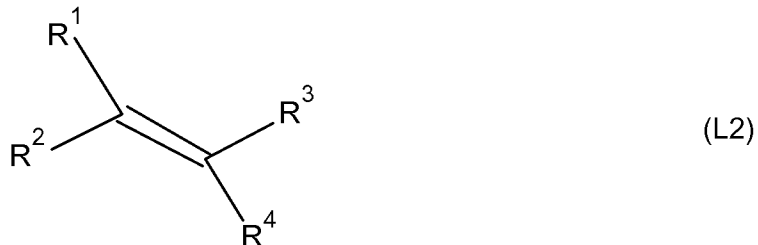
Leveling agents

The plating composition may further comprise one or more leveling agents.

5 Preferred levelers are those of formula L1 to L4

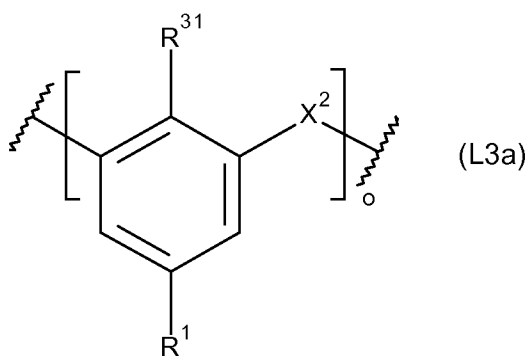


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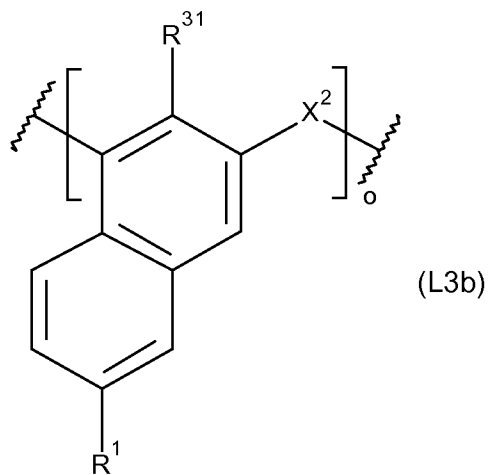


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20



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(L3b)

30



with the substituents described below.

35 As used herein, "aryl" means a C₆ to C₁₄ carbocyclic or a C₃ to C₁₀ nitrogen or oxygen containing heterocyclic aromatic ring system, which may be unsubstituted or substituted by up to three C₁ to C₁₂ alkyl groups or up to two OH, NH₂ or NO₂ groups.

40 In all embodiments, R¹ in formulas L1 to L4 may be selected from X¹-CO-O-R¹¹, X¹-SO₂-O-R¹¹, X¹-PO(OR¹¹)₂, and X¹-SO-OR¹¹. R¹ is also referred to herein as "functional group".

X¹ may be a chemical bond, which means that the functional groups -CO-O-R¹¹, -SO₂-O-R¹¹, -PO(OR¹¹)₂ and -SO-OR¹¹ are directly bonded to the polymer backbone in formula L1, the vinyl group in formula L2 or the aromatic system in formulas L3a, L3b, and L4. As used herein, "chemical bond" means that the respective moiety is not present but that the adjacent moieties are bridged so as to form a direct chemical bond between these adjacent moieties. By way of example, if in X-Y-Z the moiety Y is a chemical bond then the adjacent moieties X and Z together form a group X-Z.

In an alternative X¹ is a divalent aryl group. Preferred divalent aryl groups are phenylene, naphthalene, pyridine, or imidazole, particularly 1, 4 phenylene.

In a further alternative X¹ is a divalent C₁ to C₁₂ alkanediyl group, which may be interrupted by O atoms. As used herein, "C_x" means that the respective group comprises x numbers of C atoms. By way of example, the terms "C_x to C_y alkanediyl" and C_x to C_y alkyl mean alk(anedi)yl with a number x to y of carbon atoms and includes linear, branched (if > C₃) and cyclic alkanediyl (if >C₄).

In yet a further alternative X¹ is a divalent arylalkyl group -X¹¹-X¹²-, wherein X¹¹ is a C₁ to C₁₅ alkandiyl group bonded to the polymer backbone, vinyl group, or aromatic system, respectively, and X¹² is a divalent aryl group bonded to the functional group. Preferred arylalkyl groups may be but are not limited to benzyl (ortho, meta or para form) and 1, 2, or 3-methylpyridine. Preferably the alkanediyl part X¹¹ may be methanediyl, propanediyl, or butanediyl. Preferably the aryl part X¹² may be phenylene, naphthalene, pyridine, or imidazole, particularly 1, 4 phenylene.

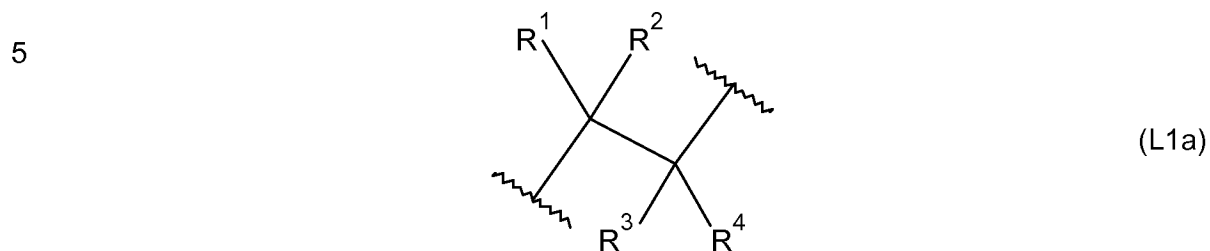
In another alternative X¹ is a divalent alkylaryl group -X¹²-X¹¹-, wherein X¹² is a divalent aryl group bonded to the polymer backbone, vinyl group, or aromatic system, respectively, and X¹¹ is a C₁ to C₁₅ alkandiyl group bonded to the functional group. Preferred arylalkyl groups may be but are not limited to toluyl (ortho, meta or para form) and 1, 2, or 3-methylpyridine. Preferably the alkanediyl part X¹¹ may be methanediyl, propanediyl, or butanediyl. Preferably the alkanediyl part X¹¹ may be phenylene, naphthalene, pyridine, or imidazole, particularly 1, 4 phenylene.

In yet another alternative X¹ is a divalent (poly)alkylene oxide spacer -(C₂H₃R¹²-O)_m-, wherein R¹² is selected from H and C₁ to C₄ alkyl, preferably H or methyl, and m is an integer from 1 to 10, preferably from 1 to 5.

Preferably, X¹ is selected from a chemical bond, C₁ to C₄ alkandiyl, or phenylene.

In a preferred embodiment R¹¹ is selected from H and C₁ to C₄ alkyl, preferably H or methyl, most preferably H.

In the first embodiment, in formula L1 is a co-monomeric unit derived from vinyl alcohol, which may optionally be (poly)ethoxylated, or acrylamide, and B is a monomeric unit of formula L1a



In formulas L1a and L2 of the first and the second embodiment, R² is selected from

- (i) H,
- (ii) aryl, preferably a C₆ to C₁₀ carbocyclic aryl or a C₃ to C₈ heterocyclic aryl comprising up to two N atoms, most preferably phenyl or pyridyl,
- 15 (iii) C₁ to C₁₀ alkyl, preferably C₁ to C₆ alkyl, more preferably C₁ to C₄ alkyl, most preferably C₁ to C₃ alkyl,
- (iv) arylalkyl, preferably a C₇ to C₁₅ carbocyclic arylalkyl or a C₄ to C₈ heterocyclic arylalkyl comprising up to two N atoms, more preferably C₄ to C₈ arylalkyl, most preferably benzyl or 1, 2, or 3-methylpyridine,
- 20 (v) alkylaryl, preferably a C₇ to C₁₅ carbocyclic alkylaryl or a C₄ to C₈ heterocyclic alkylaryl comprising up to two N atoms, more preferably C₄ to C₈ alkylaryl, most preferably toluyl (ortho, meta or para form) and 1, 2, or 3-methylpyridine, or
- (vi) a (poly)alkylene oxide substituent $-(O-C_2H_3R^{12})_m-OH$, with m being an integer from 1 to 50, preferably 1 to 30, more preferably 1 or 2 to 20, most preferably 1 or
- 25 2 to 10, and R¹².

In formulas L1a and L2, R³ is selected from R¹ and R². R⁴ is selected from R² and, only in case R³ is not R¹, R³ may also be R¹. In other words: The formulas L1a and L2 may comprise one or two functional groups R¹. As a consequence, the levelers of L2 with

30 two functional groups may have cis and trans configuration with respect to functional group R¹.

In a preferred embodiment, R², R³ and R⁴ are selected from H, methyl, ethyl, or propyl, most preferably H. In another preferred embodiment, R² and either R³ or R⁴ are

35 selected from H, methyl, ethyl, or propyl, most preferably H and the other group R³ or R⁴ is selected from R¹.

In formula L1, n is an integer from 2 to 10,000 and p may either be 0 or an integer from 1 to 10,000.

40

If p is 0, the levelers of formula L1 may be homopolymers, such as but not limited to polyacrylic acid, polysulfonic acid, polyphosphonic acid and the like, in which

$R^2=R^3=R^4=H$, or polymaleic acid, in which $R^2=R^4=H$ and $R^3=R^1$ or $R^2=R^3=H$ and $R^4=R^1$.

Alternatively, the levelers of formula L1 may be co-polymers, such as but not limited to poly(acrylic acid-co-maleic acid), poly(acrylic acid-co-2-methylacrylic acid),

poly(sulfonic acid-co-maleic acid), poly(phosphonic acid-co-maleic acid), and the like,

5 in order to tune the amount of functional groups present in the leveler.

Alternatively, if $p>0$, the polymeric levelers may be co-polymers of the monomers mentioned above with further monomers like vinyl alcohol and its ethoxylated or polyethoxylated derivatives or acrylamide. In this case the sum of n and p is the overall degree of polymerization.

10

The degree of polymerization $n+p$ in formula L1 is an integer from 2 to 10,000.

Preferably $n+p$ is an integer from 10 to 5000, most preferably from 20 to 5000.

If copolymers are used, such copolymers may have block, random, alternating or

15 gradient, preferably random structure. As used herein, "random" means that the respective co-monomers are polymerized from a mixture and therefore arranged in a statistically manner depending on their copolymerization parameters. As used herein, "block" means that the respective co-monomers are polymerized after each other to form blocks of the respective co-monomers in any predefined order.

20

The molecular weight M_w of the polymeric levelers of formula L1 may be from about 500 to about 500000 g/mol, preferably from about 1000 to about 350000 g/mol, most preferably from about 2000 to about 300000 g/mol. In one particular embodiment the molecular weight M_w is from about 1500 to about 10000 g/mol. In another embodiment

25

the molecular weight M_w is from about 15000 to about 50000 g/mol. In yet another embodiment the molecular weight M_w is from about 100000 to about 300000 g/mol.

If co-polymers are used, the ratio between two monomers B or the comonomers A and the monomers B in the levelers of formula L1 may be from 5:95 to 95:5% by weight,

30 preferably from 10:90 to 90:10 by weight, most preferably from 20:80 to 80:40 by weight. Also terpolymers comprising two monomers B and a comonomer A may be used.

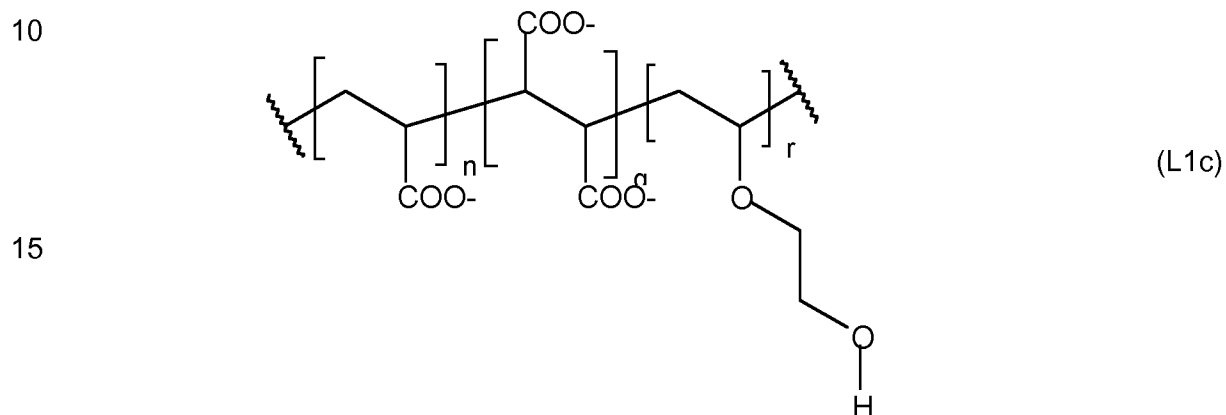
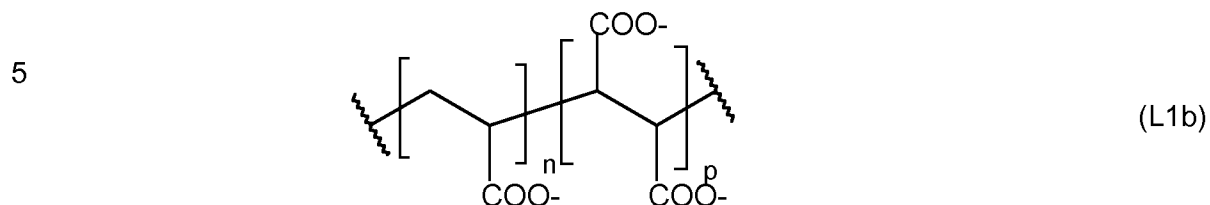
Particularly preferred polymeric levelers of formula L1 are polyacrylic acid, a maleic

35 acid acrylic acid copolymer, an acrylic acid 2-methylacrylic acid copolymer, polyphosphonic acid, and polysulfonic acid. Most preferred are polyacrylic acid, a maleic acid acrylic acid copolymer and an acrylic acid 2-methylacrylic acid copolymer. In case of a maleic acid acrylic acid copolymer a ratio $p:n$ of 20:80 to 60:40 is particularly preferred. In case of a 2-methylacrylic acid acrylic acid copolymer a ratio

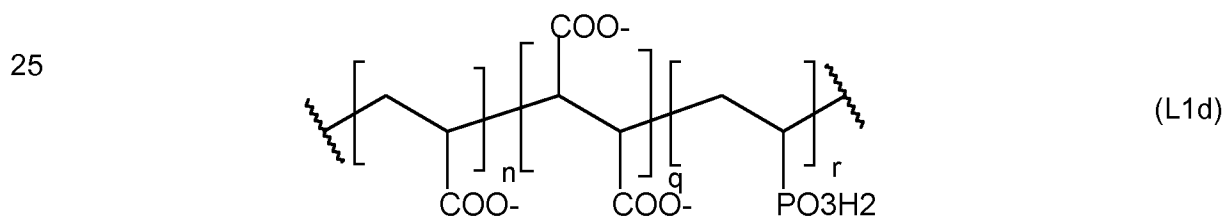
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$p:n$ of 20:80 to 80:20 is particularly preferred.

The following specific copolymer levelers of formulas L1b to L1d are particularly preferred:



20 which is a terpolymer of acrylic acid, maleic acid and ethoxylated vinyl alcohol, wherein q and r are integers, the sum q+r corresponds to p in formula 1 and the ratio q/r is from 10:90 to 90:10, preferably 20:80 to 80:40, most preferably from 40:60 to 60:40; and



30 which is a terpolymer of acrylic acid, maleic acid and vinylphosphonic acid, wherein q and r are integers, the sum q+r corresponds to p in formula 1 and the ratio q/r is from 10:90 to 90:10, preferably 20:80 to 80:40, most preferably from 40:60 to 60:40.

35 Particularly preferred monomeric levelers of formula L2 are acrylic acid, vinylphosphonic acid, and vinylsulfonic acid.

In the third embodiment comprising a polymeric leveling agent of formula L3a or L3b (together also referred to as L3) R³¹ may generally be R¹, H, OR⁵ and R⁵ as defined above. Preferably, R³¹ is H or OH. Such polymers are available in the market under

40 Naphthalene sulphonic acid condensation product, Na-salt and Phenol sulfonic acid condensation product, Na-salt, e.g. from BASF.

In the levelers of formula L3 X^2 is (i) a chemical bond or (ii) methanediyl. Preferably X^2 is methanediyl.

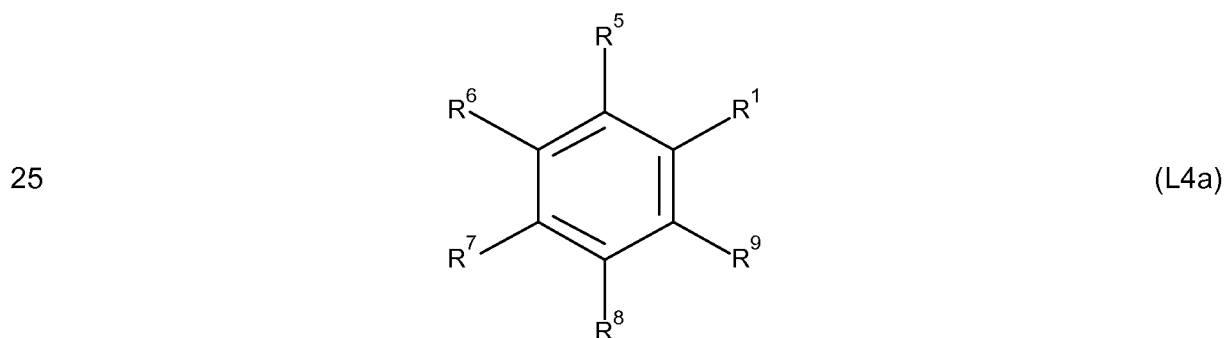
The degree of polymerization o in the levelers of formula L3 is from 2 to 1000.

- 5 Preferably o is an integer from 5 to 500, most preferably from 10 to 250.

The molecular weight M_w of the polymeric levelers L3 may be from about 500 to about 400000 g/mol, preferably from about 1000 to about 300000 g/mol, most preferably from about 3000 to about 250000 g/mol. In one particular embodiment the molecular weight M_w is from about 1500 to about 10000 g/mol. In another embodiment the molecular weight M_w is from about 15000 to about 50000 g/mol. In yet another embodiment the molecular weight M_w is from about 100000 to about 300000 g/mol.

- 10 M_w is from about 1500 to about 10000 g/mol. In another embodiment the molecular weight M_w is from about 15000 to about 50000 g/mol. In yet another embodiment the molecular weight M_w is from about 100000 to about 300000 g/mol.
- 15 In the fourth embodiment the levelers of formula L4 $\emptyset$ is a C_6 to C_{14} carbocyclic or a C_3 to C_{10} nitrogen or oxygen containing heterocyclic aryl group, which may be unsubstituted or substituted by up to three C_1 to C_{12} alkyl groups or up to two OH, NH_2 or NO_2 groups. Preferably the heterocyclic aryl groups are 5 or 6 membered rings systems with up to 2, preferably 1, N atoms.

- 20 Preferred groups $\emptyset$ are those of formula L4a



- 30 wherein R^5 , R^6 , R^7 , R^8 , and R^9 are independently selected from (i) H and (ii) C_1 to C_6 alkyl. Preferably R^5 , R^6 , R^8 , and R^9 are independently selected from H, methyl, ethyl or propyl, most preferably H. Preferably R^7 is selected from H, methyl, ethyl or propyl, most preferably from methyl or ethyl.

- 35 In certain embodiments, the leveler may be present at a concentration between about 1-10,000 ppm, or between about 10-1,000 ppm, or between about 10-500 ppm. In some cases, the concentration of leveler may be at least about 1 ppm, or at least about 100 ppm. In these or other cases, the concentration of leveler may be about 500 ppm or less, or about 1000 ppm or less.

40

In one embodiment a single leveling agent may be used in the cobalt electroplating baths, i.e. the bath is essentially free from any further leveling agent as described in the

section below. In another embodiment two or more of the leveling agents are used in combination.

Other levelers often contain one or more nitrogen, amine, imide or imidazole, and may also contain sulfur functional groups. Certain levelers include one or more five and six member rings and/or conjugated organic compound derivatives. Nitrogen groups may form part of the ring structure. In amine-containing levelers, the amines may be primary, secondary or tertiary alkyl amines. Furthermore, the amine may be an aryl amine or a heterocyclic saturated or aromatic amine. Example amines include, but are not limited to, dialkylamines, trialkylamines, arylalkylamines, triazoles, imidazole, triazole, tetrazole, benzimidazole, benzotriazole, piperidine, morpholines, piperazine, pyridine, oxazole, benzoxazole, pyrimidine, quonoline, and isoquinoline. Imidazole and pyridine may be useful in some cases. Other examples of levelers include Janus Green B and Prussian Blue. Leveler compounds may also include ethoxide groups. For example, the leveler may include a general backbone similar to that found in polyethylene glycol or polyethylene oxide, with fragments of amine functionally inserted over the chain (e.g., Janus Green B). Example epoxides include, but are not limited to, epihalohydrins such as epichlorohydrin and epibromohydrin, and polyepoxide compounds. Polyepoxide compounds having two or more epoxide moieties joined together by an ether-containing linkage may be useful in some cases. Some leveler compounds are polymeric, while others are not. Example polymeric leveler compounds include, but are not limited to, polyethylenimine, polyamidoamines, and reaction products of an amine with various oxygen epoxides or sulfides. One example of a non-polymeric leveler is 6-mercapto-hexanol. Another example leveler is polyvinylpyrrolidone (PVP).

Further levelers that may be particularly useful in the context of cobalt are, but are not limited to: alkylated polyalkyleneimines; polyethylene glycol; organic sulfonates; 4-mercaptopyridine; 2-mercaptothiazoline; ethylene thiourea; thiourea; 1-(2-hydroxyethyl)-2-imidazolidinethion; sodium naphthalene 2-sulphonate; acrylamide; substituted amines; imidazole; triazole; tetrazole; piperidine; morpholine; piperazine; pyridine; oxazole; benzoxazole; quinolin; isoquinoline; coumarin and derivatives thereof.

35 Accelerating Agents

The plating composition may further comprise one or more accelerating agents (also referred to as accelerators), preferably in combination with a suppressing agent.

Example accelerators that may be useful for depositing cobalt include, but are not limited to: N,N-dimethyldithiocarbamic acid (-3-sulfopropyl)ester; 3-mercapto-propylsulfonic acid-(3-sulfurpropyl) ester; 3-sulfanyl-1-propane sulfonate; carbonic acid-

dithio-o-ethylester-s-ester with 3-mercapto-1-propane sulfonic acid potassium salt; bis-sulfopropyl disulfide; 3-(benzothiazolyl-s-thio)propyl sulfonic acid sodium salt; pyridinium propyl sulfobetaine; l-sodium-3-mercaptopropane-l-sulfonate; N,N-dimethyl-dithiocarbamic acid-(3-sulfoethyl)ester; 3-mercapto-ethyl propylsulfonic acid (3-sulfoethyl)ester; 3-mercapto-ethylsulfonic acid sodium salt; carbonic acid-dithio-o-ethyl ester-s-ester; pyridinium ethyl sulfobetaine; and thiourea. In some cases a combination of these accelerators is used. In a particular embodiment the accelerator is 3-sulfanyl-1-propane sulfonate (commonly referred to as MPS or 3-mercapto-1-propane sulfonic acid sodium salt) and/or thiourea (TU). The accelerator chosen may include, in some cases, a sulfonic acid component and/or an ester component and/or a thiol group.

In some embodiments, the accelerator is present in electrolyte at a concentration between about 1-10,000 ppm, for example between about 150-500 ppm, or between about 150-400 ppm. In some embodiments, the concentration of accelerator is at least about 100 ppm, at least about 150 ppm, at least about 200 ppm, or at least about 300 ppm. In these or other cases, the concentration of accelerator may be about 1,000 ppm or less, or about 500 ppm or less, or about 400 ppm or less. The optimal accelerator concentration may depend on the identity of the accelerator that is used. In various embodiments, the accelerator is MPS and is present in electrolyte at a concentration that meets one or more of the limitations set out in this paragraph. In certain other embodiments, the accelerator is thiourea and is present in electrolyte at a concentration that meets one or more of the limitations set out in this paragraph.

In one embodiment the cobalt electroplating composition is free of any accelerating agent. Preferably the composition is free of any sulfur containing compound.

Other Additives

A large variety of further additives may typically be used in the bath to provide desired surface finishes for the Co plated metal. Usually more than one additive is used with each additive forming a desired function. Advantageously, the electroplating baths may contain one or more of wetting agents or surfactants like Lutensol®, Plurafac® or Pluronic® (available from BASF) to get rid of trapped air or hydrogen bubbles and the like. Further components to be added are grain refiners, stress reducers, levelers and mixtures thereof.

The bath may also contain a complexing agent for the cobalt ions, such as but not limited to sodium acetate, sodium citrate, EDTA, sodium tartrate, or ethylene diamine.

Further additives are disclosed in Journal of The Electrochemical Society, 156 (8) D301-D309 2009 "Superconformal Electrodeposition of Co and Co-Fe Alloys Using 2-Mercapto-5-benzimidazolesulfonic Acid", which is incorporated herein by reference.

- 5 In a further embodiment, surfactants may be present in the electroplating composition in order to improve wetting. Wetting agents may be selected from nonionic surfactants, anionic surfactants and cationic surfactants.

- 10 In a preferred embodiment non-ionic surfactants are used. Typical non-ionic surfactants are fluorinated surfactants, polyglycols, or poly oxyethylene and/or oxypropylene containing molecules.

- 15 In a preferred embodiment the cobalt or cobalt alloy electroplating composition consists essentially of cobalt ions (and the respective counter ions and precursors), the ammonium compound, a suppressing agent, a leveling agent, and optionally an acid except boric acid.

Electrolyte

- 20 In one embodiment, the usually aqueous plating bath used for void-free filling with cobalt or cobalt alloys may contain a cobalt ion source, such as but not limited to cobalt sulfate, cobalt chloride, or cobalt sulfamate.

- 25 The cobalt ion concentration within the electroplating solution may be in a range of 0.01 to 1 mol/l. In one particular example, the ion concentration can have a range of 0.1 to 0.6 mol/l. In another particular example, the range can be from 0.3 to 0.5 mol/l. In yet another particular example, the range can be from 0.03 to 0.1 mol/l.

- 30 In a preferred embodiment the composition is essentially free from chloride ions. Essentially free from chloride means that the chloride content is below 1 ppm, particularly below 0.1 ppm.

- 35 During deposition, the pH of the plating bath may be adjusted to have a high Faradaic efficiency while avoiding the co-deposition of cobalt hydroxides. For this purpose, a pH range of 1 to 6 may be employed. In a particular example pH range of 2 to 5.5 can be employed. In another particular example, a pH range of 3 to 5.5 can be used. Preferably the pH is below 5, most preferably below 4.

- 40 In a preferred embodiment boric acid may be used in the cobalt electroplating bath as supporting electrolyte. Boric acid may be incorporated into the composition in a concentration between about 5 and about 50 g/l, such as between about 15 and about 40 g/l.

The electrodeposition composition is preferably free of nickel ions and iron ions. If either nickel ions or iron ions are present, the molar ratio of both nickel ions and iron ions, and the sum of nickel ions and iron ions, to cobalt ions is preferably not greater than about 0.01, or between about 0.00001 and about 0.01.

The electrodeposition composition is also preferably substantially free of copper ions. Although very minor copper contamination may be difficult to avoid, it is particularly preferred that the copper ion content of the bath is no more than 20 ppb, e.g., in the range of 0.1 ppb to 20 ppb.

The electrodeposition composition is preferably free of any functional concentration of reducing agents effective to reduce cobaltous ion (Co^{2+}) to metallic cobalt (Co^0). By a functional concentration is meant any concentration of an agent that either is effective to reduce cobaltous ions in the absence of electrolytic current or is activated by an electrolytic current or electrolytic field to react with cobaltous ions.

Process

An electrolytic bath is prepared comprising cobalt ions and the at least one additive according to the invention. For interconnects a dielectric substrate having the seed layer is placed into the electrolytic bath where the electrolytic bath contacts the at least one outer surface and the three dimensional pattern having a seed layer in the case of a dielectric substrate. A counter electrode is placed into the electrolytic bath and an electrical current is passed through the electrolytic bath between the seed layer on the substrate and the counter electrode. At least a portion of cobalt is deposited into at least a portion of the three dimensional pattern wherein the deposited cobalt is substantially void-free.

The present invention is useful for depositing a layer comprising cobalt on a variety of substrates, particularly those having micrometer and/or nanometer and particularly variously sized apertures. For example, the present invention is particularly suitable for depositing cobalt on integrated circuit substrates, such as semiconductor devices, with small diameter vias, trenches or other apertures. In one embodiment, semiconductor devices are plated according to the present invention. Such semiconductor devices include, but are not limited to, wafers used in the manufacture of integrated circuits. Furthermore, the present invention is particularly suitable for depositing cobalt for under bump metallization purposes.

In order to allow a deposition on a substrate comprising a dielectric surface a seed layer needs to be applied to the surface. Such seed layer may consist of cobalt, iridium, osmium, palladium, platinum, rhodium, and ruthenium or alloys comprising such

metals. Preferred is the deposition on a cobalt seed. The seed layers are described in detail e.g. in US20140183738 A.

The seed layer may be deposited or grown by chemical vapor deposition (CVD).
5 atomic layer deposition (ALD), physical vapor deposition (PVD). Electroplating, electroless plating or other suitable process that deposits conformal thin films. In an embodiment, the cobalt seed layer is deposited to form a high quality conformal layer that sufficiently and evenly covers all exposed surfaces within the openings and top surfaces. The high quality seed layer may be formed, in one embodiment, by
10 depositing the cobalt seed material at a slow deposition rate to evenly and consistently deposit the conformal seed layer. By forming the seed layer in a conformal manner, compatibility of a subsequently formed fill material with the underlying structure may be improved. Specifically, the seed layer can assist a deposition process by providing appropriate surface energetics for deposition thereon.

15 Preferably the substrate comprises submicrometer sized features and the cobalt deposition is performed to fill the submicrometer sized features. Most preferably the submicrometer-sized features have an (effective) aperture size of 10 nm or below and/or an aspect ratio of 4 or more. More preferably the features have an aperture size
20 of 7 nanometers or below, most preferably of 5 nanometers or below.

The aperture size according to the present invention means the smallest diameter or free distance of a feature before plating, i.e. after seed deposition. The terms "aperture" and "opening" are used herein synonymously.

25 The electrodeposition current density should be chosen to promote the void-free, particularly the bottom-up filling behavior. A range of 0.1 to 40 mA/cm² is useful for this purpose. In a particular example, the current density can range from 1 to 10 mA/cm². In another particular example, the current density can range from 5 to 15 mA/cm².

30 The general requirements for a process of cobalt electrodeposition on semiconductor integrated circuit substrates is described in US 2011/0163449 A1.

Typically, substrates are electroplated by contacting the substrate with the plating
35 baths of the present invention. The substrate typically functions as the cathode. The plating bath contains an anode, which may be soluble or insoluble. Optionally, cathode and anode may be separated by a membrane. Potential is typically applied to the cathode. Sufficient current density is applied and plating performed for a period of time sufficient to deposit a metal layer, such as a cobalt layer, having a desired thickness on
40 the substrate. Suitable current densities include, but are not limited to, the range of 1 to 250 mA/cm². Typically, the current density is in the range of 1 to 60 mA/cm² when used to deposit cobalt in the manufacture of integrated circuits. The specific current density

depends on the substrate to be plated, the leveling agent selected and the like. Such current density choice is within the abilities of those skilled in the art. The applied current may be a direct current (DC), a pulse current (PC), a pulse reverse current (PRC) or other suitable current.

5

In general, when the present invention is used to deposit metal on a substrate such as a wafer used in the manufacture of an integrated circuit, the plating baths are agitated during use. Any suitable agitation method may be used with the present invention and such methods are well-known in the art. Suitable agitation methods include, but are not limited to, inert gas or air sparging, work piece agitation, impingement and the like. Such methods are known to those skilled in the art. When the present invention is used to plate an integrated circuit substrate, such as a wafer, the wafer may be rotated such as from 1 to 300 RPM and the plating solution contacts the rotating wafer, such as by pumping or spraying. In the alternative, the wafer need not be rotated where the flow of the plating bath is sufficient to provide the desired metal deposit.

Cobalt is deposited in apertures according to the present invention without substantially forming voids within the metal deposit.

As used herein, void-free fill may either be ensured by an extraordinarily pronounced bottom-up cobalt growth while perfectly suppressing the sidewall cobalt growth, both leading to a flat growth front and thus providing substantially defect free trench/via fill (so-called bottom-up-fill) or may be ensured by a so-called V-shaped filling.

As used herein, the term "substantially void-free", means that at least 95% of the plated apertures are void-free. Preferably that at least 98% of the plated apertures are void-free, mostly preferably all plated apertures are void-free. As used herein, the term "substantially seam-free", means that at least 95% of the plated apertures are seam-free. Preferably that at least 98% of the plated apertures are seam-free, mostly preferably all plated apertures are seam-free.

Plating equipment for plating semiconductor substrates are well known. Plating equipment comprises an electroplating tank which holds Co electrolyte and which is made of a suitable material such as plastic or other material inert to the electrolytic plating solution. The tank may be cylindrical, especially for wafer plating. A cathode is horizontally disposed at the upper part of tank and may be any type substrate such as a silicon wafer having openings such as trenches and vias. The wafer substrate is typically coated with a seed layer of Co or other metal or a metal containing layer to initiate plating thereon. An anode is also preferably circular for wafer plating and is horizontally disposed at the lower part of tank forming a space between the anode and cathode. The anode is typically a soluble anode.

These bath additives are useful in combination with membrane technology being developed by various tool manufacturers. In this system, the anode may be isolated from the organic bath additives by a membrane. The purpose of the separation of the anode and the organic bath additives is to minimize the oxidation of the organic bath additives.

The cathode substrate and anode are electrically connected by wiring and, respectively, to a rectifier (power supply). The cathode substrate for direct or pulse current has a net negative charge so that Co ions in the solution are reduced at the cathode substrate forming plated Co metal on the cathode surface. An oxidation reaction takes place at the anode. The cathode and anode may be horizontally or vertically disposed in the tank.

While the process of the present invention has been generally described with reference to semiconductor manufacture, it will be appreciated that the present invention may be useful in any electrolytic process where a substantially void-free cobalt deposit is desired. Such processes include printed wiring board manufacture. For example, the present plating baths may be useful for the plating of vias, pads or traces on a printed wiring board, as well as for bump plating on wafers. Other suitable processes include packaging and interconnect manufacture. Accordingly, suitable substrates include lead frames, interconnects, printed wiring boards, and the like.

All percent, ppm or comparable values refer to the weight with respect to the total weight of the respective composition except where otherwise indicated. All cited documents are incorporated herein by reference.

The following examples shall further illustrate the present invention without restricting the scope of this invention.

Examples

Experimental Methods

The experiments were performed by using a 300 mm silicon wafer segment with a patterned photoresist 56 μm thick and a plurality of copper seeded 50 micrometer opening vias (available from IMAT, Inc., Vancouver, WA, USA).

The electroplated cobalt was investigated by a 3D laser scanning microscope (3D LSM). The height of the deposited cobalt layer in the bumps was determined visually.

The non-uniformity was determined from heights of the 82, bumps:
(a) 70 bumps in the dense area at two locations:

- (i) 35 bumps at the center of the dense area with a pitch size of 100 μm and an open bump area of 19.6 %, and
- (ii) 35 bumps at the edge of the dense area with a pitch size of 150 μm and an open bump area of 8.7 %, and
- (b) 12 bumps at the isolated area with a pitch size of 250 μm and an open bump area of 3.1 %.

The non-uniformity was calculated from the heights by using the following formula:

$$\text{Non-U [\%]} = \frac{\text{Max. bump height} - \text{min. bump height}}{2 * \text{mean height}} \times 100$$

wherein

“Max. bump height” and “min. bump height” are the height of cobalt deposit in the bump with the highest and the lowest deposited cobalt layer, respectively, and

“mean height” means the arithmetic average of all heights.

Example 1 (Comparative)

A cobalt electroplating bath containing 1.02 mol/l $\text{CoSO}_4 \cdot 7\text{H}_2\text{O}$ in DI water was prepared. The pH of the solution is 5.3.

Cobalt was electroplated from the plating bath onto the wafer by contacting and rotating the substrate at 100 rpm at 25 °C and applying a current of 100 mA/cm² for 360 s.

The non-uniformity of the Co film was 52.2%.

Example 2 (Comparative)

A cobalt electroplating bath containing 1.02 mol/l $\text{CoSO}_4 \cdot 7\text{H}_2\text{O}$, 0.49 mol/l H_3BO_3 , in DI water was prepared. The pH of the solution was 3.9.

Cobalt was electroplated from the plating bath onto the wafer by contacting and rotating the substrate at 100 rpm at 25 °C and applying a current of 100 mA/cm² for 360 s.

The non-uniformity of the Co film was 39.8%. The non-uniformity was only slightly reduced in comparison with comparative example 1.

Example 3

A cobalt electroplating bath containing 1.02 mol/l $\text{CoSO}_4 \cdot 7\text{H}_2\text{O}$, 0.50 mol/l NH_4Cl , in DI water was prepared. The pH of the solution was 4.1.

5 Cobalt was electroplated from the plating bath onto the wafer by contacting and rotating the substrate at 100 rpm at 25 °C and applying a current of 100 mA/cm² for 360 s.

10 The non-uniformity of the Co film was 21.6%. By using NH_4Cl the non-uniformity was reduced by approx. 60% in relation to comparative example 1 (no additive) and approx. 46% in relation to comparative example 2 (use of boric acid).

Example 4

15 A cobalt electroplating bath containing 1.02 mol/l $\text{CoSO}_4 \cdot 7\text{H}_2\text{O}$, 0.50 mol/l $\text{NH}_4\text{CH}_3\text{COO}$, in DI water was prepared. The pH of the solution was 5.8.

20 Cobalt was electroplated from the plating bath onto the wafer by contacting and rotating the substrate at 100 rpm at 25 °C and applying a current of 100 mA/cm² for 360 s.

The non-uniformity of the Co film was 30.2%. By using $\text{NH}_4\text{CH}_3\text{COO}$ the non-uniformity was reduced by approx. 42% in relation to comparative example 1 (no additive) and approx. 24% in relation to comparative example 2 (use of boric acid).

Claims

1. A composition comprising
 - (a) cobalt ions,
 - (b) an ammonium compound of formula $(NR^1R^2R^3H^+)_n X^{n-}$
 wherein

R^1, R^2, R^3 are independently selected from H and linear or branched C_1 to C_6 alkyl,

X is selected from an n valent inorganic or organic counter ion,

n is an integer selected from 1, 2 or 3.
2. A composition according to claim 1, wherein R^1, R^2 , and R^3 are independently selected from H and a linear or branched C_1 to C_4 alkyl.
3. A composition according to anyone of the preceding claims, wherein at least two of R^1, R^2 and R^3 are H, preferably all of R^1, R^2 , and R^3 are H.
4. A composition according to anyone of the preceding claims, wherein X is an inorganic counter-ion, particularly chloride, sulfate, hydrogen sulfate, phosphate, hydrogen phosphate, dihydrogen phosphate, and nitrate.
5. A composition according to anyone of the preceding claims, wherein X is chloride.
6. A composition according to anyone of claims 1 to 3, wherein X is an organic counter-ion, particularly C_1 to C_6 alkyl sulfonate, C_1 to C_6 carboxylates, phosphonates, and sulfamates.
7. A composition according anyone of the preceding claims further comprising a suppressing agent of formula S1



wherein

R^1 is selected from X-Y;

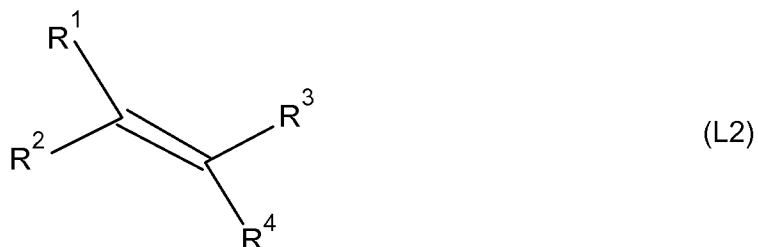
R^2 is selected from R^1 and R^3 ;

- X is selected from linear or branched C₁ to C₁₀ alkanediyl, linear or branched C₂ to C₁₀ alkenediyl, linear or branched C₂ to C₁₀ alkynediyl, and (C₂H₃R⁶-O)_m-H;
- Y is selected from OR³, NR³R⁴, N⁺R³R⁴R⁵ and NH-(C=O)-R³;
- 5 R³, R⁴, R⁵ are the same or different and are selected from (i) H, (ii) C₅ to C₂₀ aryl, (iii) C₁ to C₁₀ alkyl (iv) C₆ to C₂₀ arylalkyl, (v) C₆ to C₂₀ alkylaryl, which may be substituted by OH, SO₃H, COOH or a combination thereof, and (vi) (C₂H₃R⁶-O)_n-H, and wherein R³ and R⁴ may together form a ring system, which may be interrupted by O or NR⁷;
- 10 m, n are integers independently selected from 1 to 30;
- R⁶ is selected from H and C₁ to C₅ alkyl;
- R⁷ is selected from R⁶ and X≡R₃.
8. A composition according anyone of the preceding claims further comprising a leveling agent comprising the structure of formula L1
- 15



or having the structure of formula L2

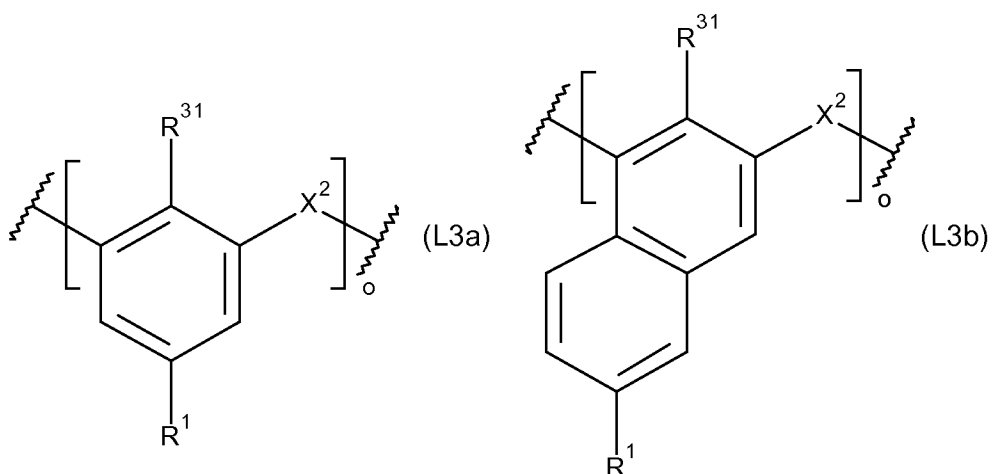
20



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or comprising the structure of formula L3a or L3b

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or having the structure of formula L4



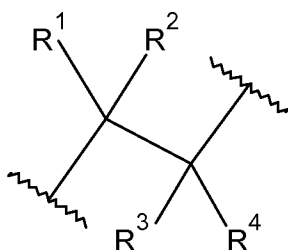
and their salts,

wherein

- 5 R^1 is selected from X^1 -CO-O- R^{11} , X^1 -SO₂-O- R^{11} , X^1 -PO(OR¹¹)₂, X^1 -SO-O- R^{11} ;
 R^2 are independently selected from (i) H, (ii) aryl, (iii) C₁ to C₁₀ alkyl (iv) arylalkyl, (v) alkylaryl, and (vi) -(O-C₂H₃R¹²)_m-OH,
 R^3 is selected from R^1 and R^2 ;
 R^4 is selected from R^2 and, in case R^3 is R^2 , R^4 may also be R^1 ,
 10 $\emptyset$ is a C₆ to C₁₄ carbocyclic or a C₃ to C₁₀ nitrogen or oxygen containing heterocyclic aryl group, which may be unsubstituted or substituted by up to three C₁ to C₁₂ alkyl groups or up to two OH, NH₂ or NO₂ groups,
 R^{31} is selected from R^1 , H, OR⁵ and R^5 ,
 X^1 is a divalent group selected from (i) a chemical bond (ii) aryl, (iii) C₁ to C₁₂ alkandiyl, which may be interrupted by O atoms, (iv) arylalkyl group - X^{11} - X^{12} -, (v) alkylaryl group - X^{12} - X^{11} -, and (vi) -(O-C₂H₃R¹²)_mO-,
 15 X^2 is (i) a chemical bond or (ii) methanediyl,
 R^{11} is selected from H and C₁ to C₄ alkyl,
 R^{12} is selected from H and C₁ to C₄ alkyl,
 20 X^{12} is a divalent aryl group,
 X^{11} is a divalent C₁ to C₁₅ alkandiyl group,
 A is a co-monomer selected from vinyl alcohol, which may optionally be (poly)ethoxylated, and acrylamide,
 B is selected from formula L1a

(L1a)

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- n is an integer from 2 to 10,000,
 m is an integer from 2 to 50,
 o is an integer from 2 to 1000, and
 p is 0 or an integer from 1 to 10,000.

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9. The composition according to claim 8, wherein the leveler is selected from polyacrylic acid, a maleic acid acrylic acid copolymer, polyphosphonic acid, polysulfonic acid, acrylic acid, vinylphosphonic acid, vinylsulfonic acid, and p-toluol sulfonate.

10. The composition according to anyone of the preceding claims, wherein the composition further comprises a suppressing agent selected from a hydroxy alkyne, C₁ to C₆ alkoxy alkyne or an amino alkyne.
- 5
11. The composition according to anyone of the preceding claims, wherein the composition is essentially boric acid free.
12. Use of a composition according to anyone of the preceding claims for depositing cobalt into interconnect features or for providing a cobalt under bump metallization.
- 10
13. A process for depositing cobalt on a semiconductor substrate comprising a recessed feature having an aperture size of 1 nanometer to 100 micrometers, the process comprising
- 15
- (a) bringing a composition according to anyone of claims 1 to 11 into contact with the semiconductor substrate,
- (b) applying a potential for a time sufficient to fill the recessed feature with cobalt.
- 20